



IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





BT137-800G0T

4Q Triac

13 March 2014

Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in general purpose bidirectional switching and phase control applications. It is used in applications where "high junction operating temperature capability" is required, the maximum rated junction temperature is 150 °C.

2. Features and benefits

- High blocking voltage capability
- Least sensitive gate for highest noise immunity
- High junction operating temperature capability
- High minimum I_{GT} for guaranteed immunity to gate noise
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

3. Applications

- Applications subject to high temperature
- General purpose motor controls
- Lighting controls
- Applications where only positive gate drive is available
- Applications where gate noise or interference may occur

4. Quick reference data

Table 1. Quick reference data

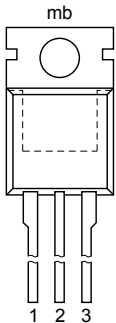
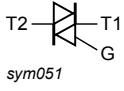
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(Init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	65	A
T_j	junction temperature		-	-	150	°C
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 127\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	8	A
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 7	10	-	50	mA



Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	10	-	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	10	-	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	10	-	100	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_j = 150\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	200	-	-	V/ μs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p style="text-align: center;">TO-220AB (SOT78)</p>	 <p style="text-align: center;"><i>sym051</i></p>
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT137-800G0T	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Marking

Table 4. Marking codes

Type number	Marking code
BT137-800G0T	BT137-800G0T

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 127\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	65	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	71	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse	-	21	A ² s
di_T/dt	rate of rise of on-state current	$I_T = 12\text{ A}$; $I_G = 0.2\text{ A}$; $dI_G/dt = 0.2\text{ A}/\mu\text{s}$; T2+ G+	-	50	A/ μs
		$I_T = 12\text{ A}$; $I_G = 0.2\text{ A}$; $dI_G/dt = 0.2\text{ A}/\mu\text{s}$; T2+ G-	-	50	A/ μs
		$I_T = 12\text{ A}$; $I_G = 0.2\text{ A}$; $dI_G/dt = 0.2\text{ A}/\mu\text{s}$; T2- G-	-	50	A/ μs
		$I_T = 12\text{ A}$; $I_G = 0.2\text{ A}$; $dI_G/dt = 0.2\text{ A}/\mu\text{s}$; T2- G+	-	10	A/ μs
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	°C
T_j	junction temperature		-	150	°C

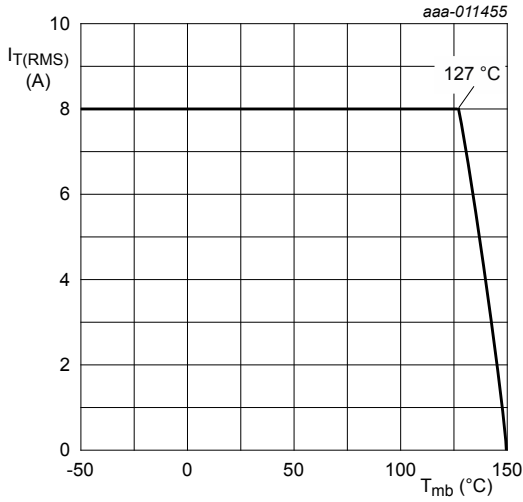
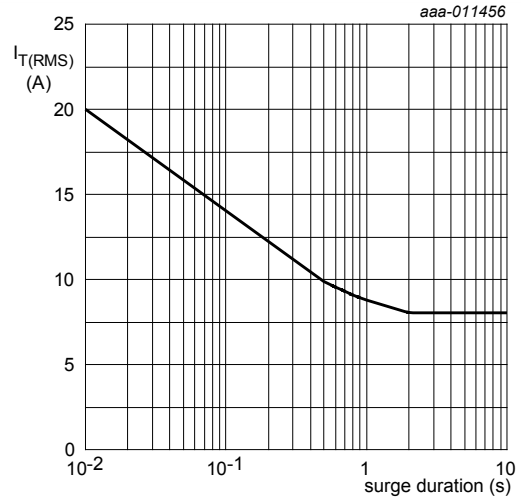


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz; T_{mb} ≤ 127 °C

Fig. 2. RMS on-state current as a function of surge duration; maximum values

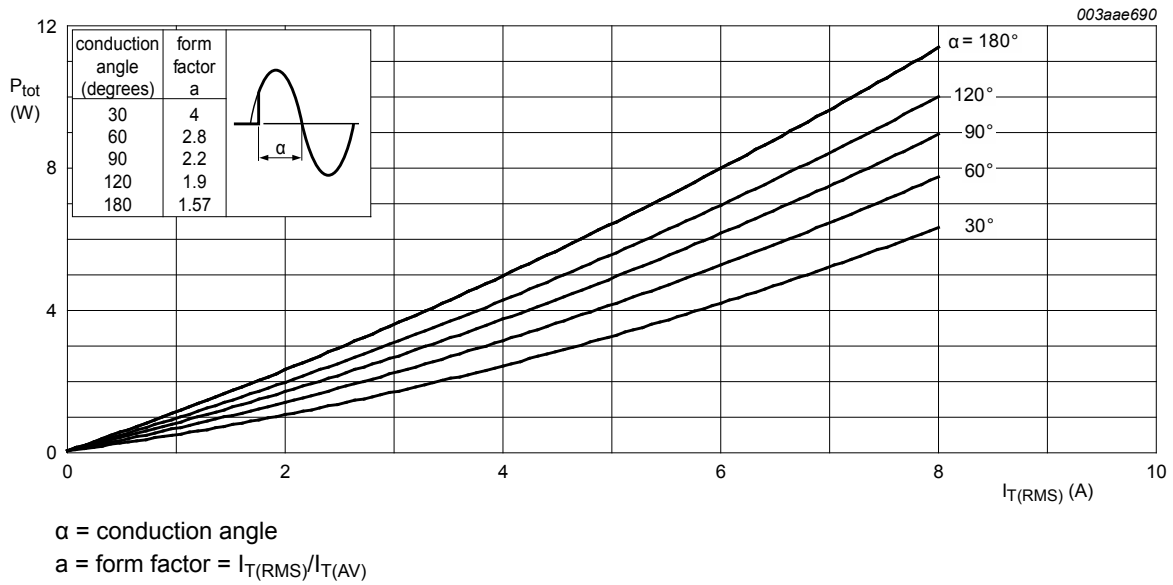


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

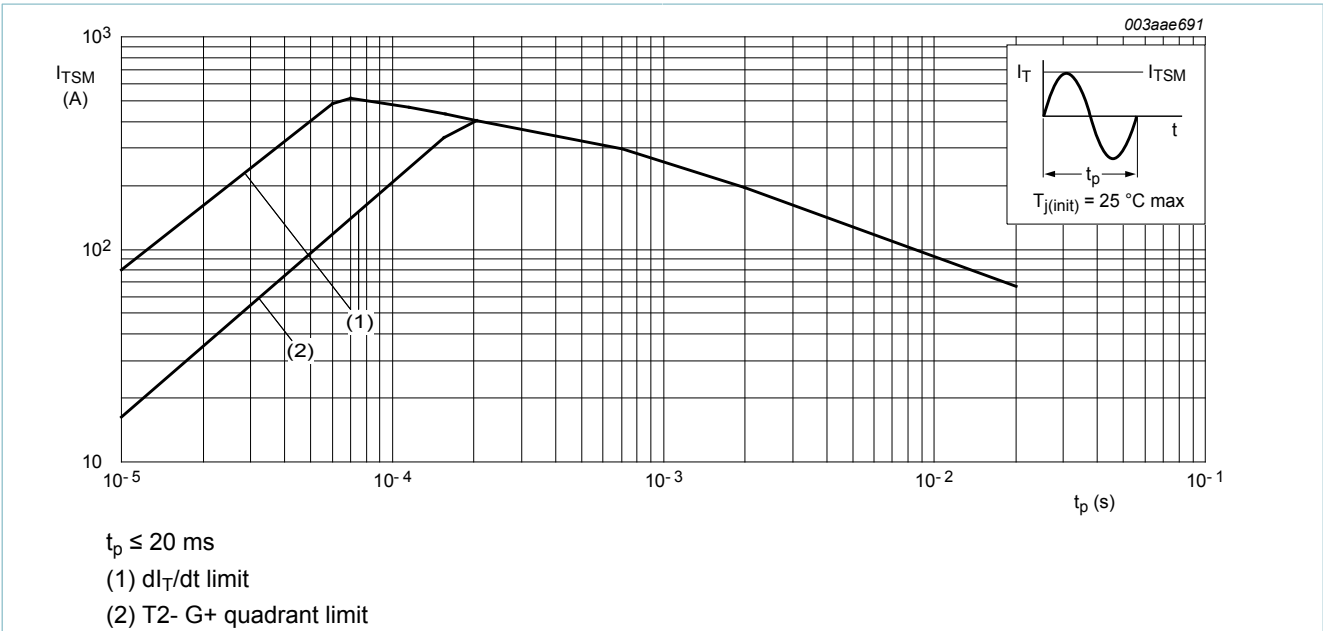


Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

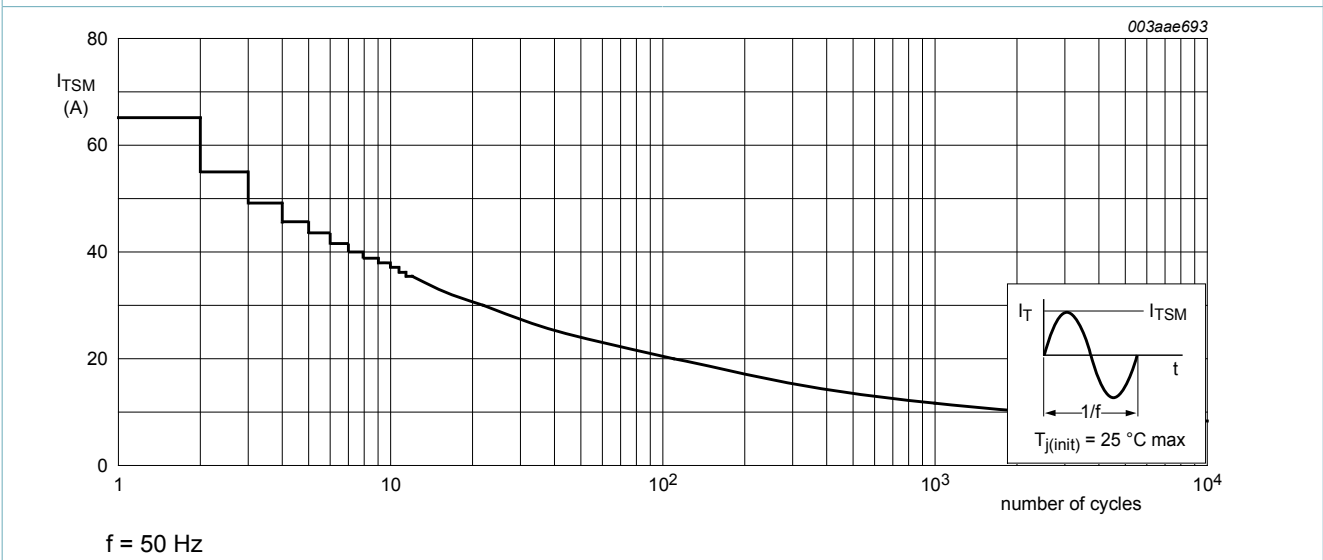


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	2	K/W
		half cycle; Fig. 6	-	-	2.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

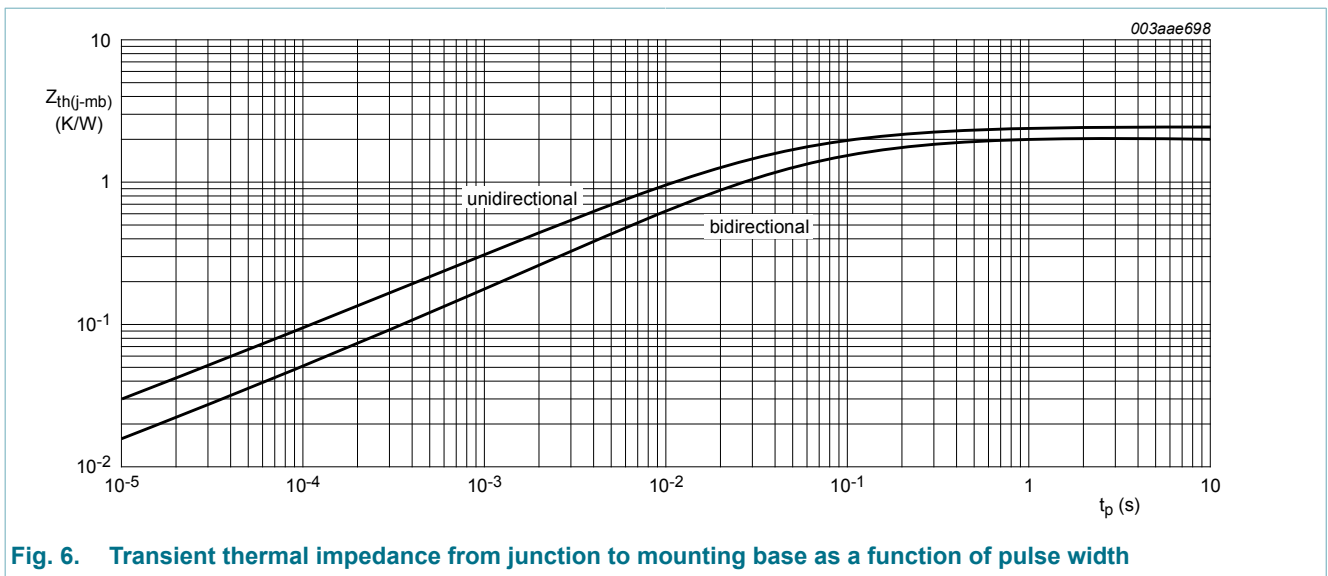


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 7	10	-	50	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7	10	-	50	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7	10	-	50	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; Fig. 7	10	-	100	mA
I _L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 8	-	-	45	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 8	-	-	60	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; Fig. 8	-	-	45	mA
		V _D = 12 V; I _G = 0.1 A; T2- G+; T _j = 25 °C; Fig. 8	-	-	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 9	-	-	40	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; Fig. 10	-	1.3	1.65	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 150 °C; Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 150 °C	-	0.4	2	mA
Dynamic characteristics						
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _j = 150 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	200	-	-	V/μs
dV _{com} /dt	rate of change of commutating voltage	V _D = 400 V; T _j = 150 °C; dI _{com} /dt = 3.6 A/ms; I _T = 8 A; gate open circuit	10	-	-	V/μs
t _{gt}	gate-controlled turn-on time	I _{TM} = 12 A; V _D = 800 V; I _G = 0.1 A; dI _G /dt = 5 A/μs	-	2	-	μs

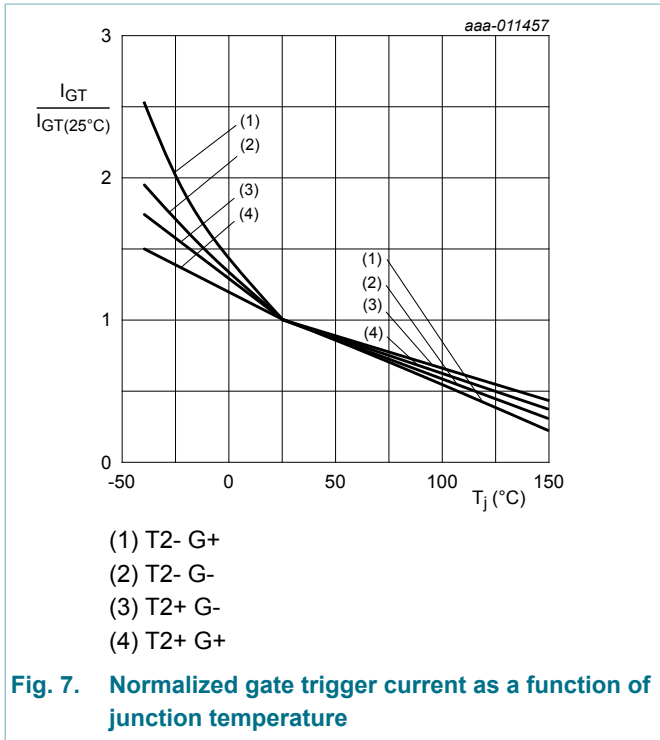


Fig. 7. Normalized gate trigger current as a function of junction temperature

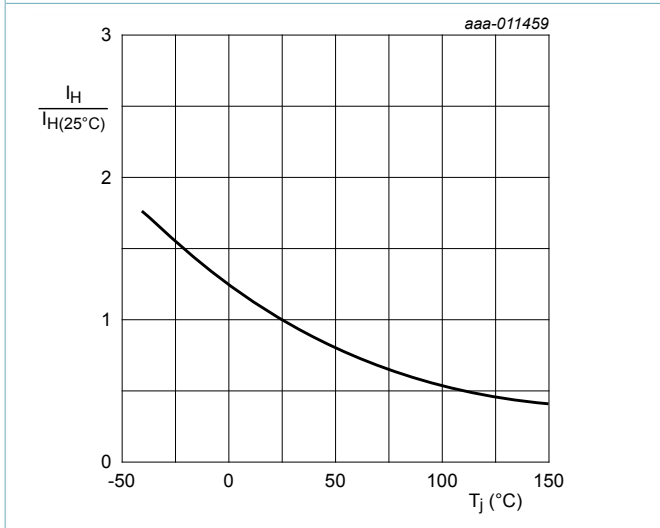


Fig. 9. Normalized holding current as a function of junction temperature

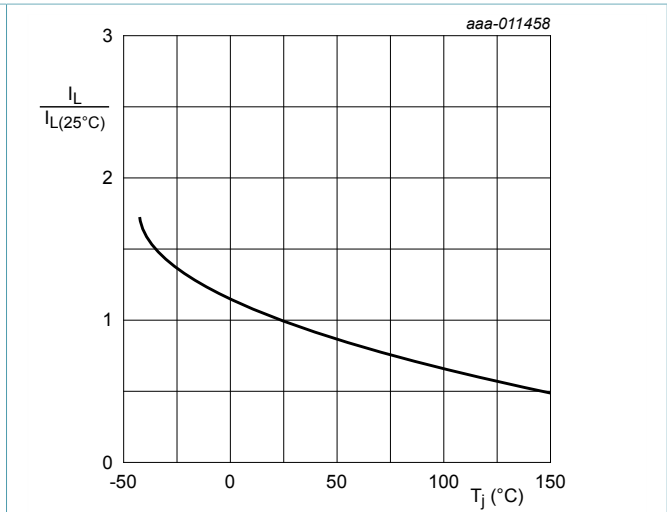


Fig. 8. Normalized latching current as a function of junction temperature

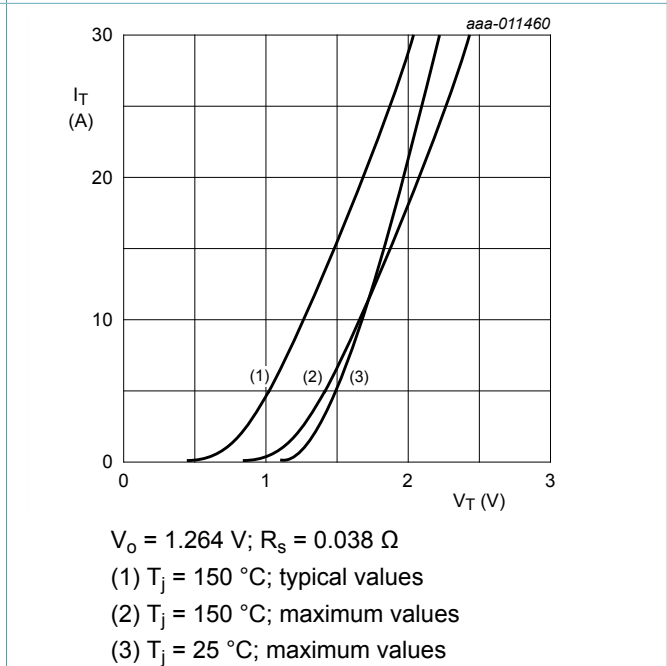


Fig. 10. On-state current as a function of on-state voltage

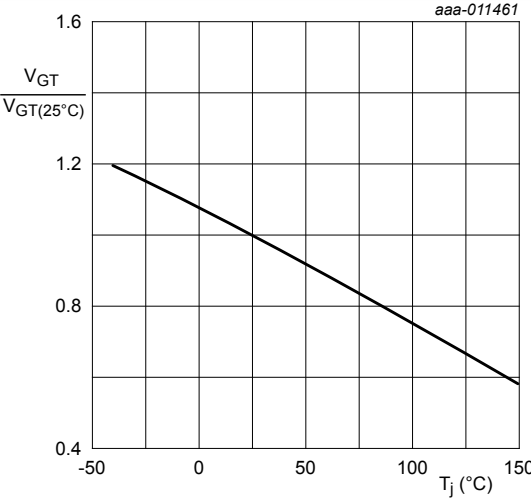
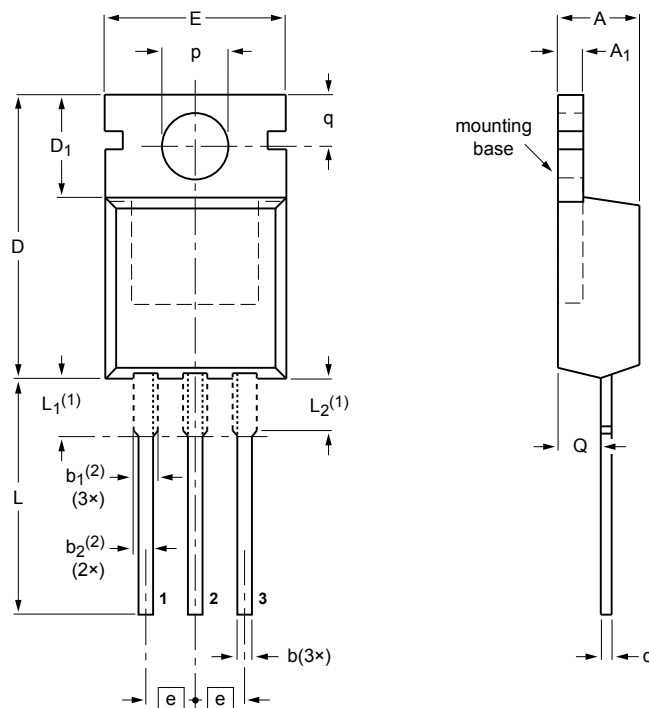


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ (2)	b ₂ (2)	c	D	D ₁	E	e	L	L ₁ (1)	L ₂ (1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig. 12. Package outline TO-220AB (SOT78)

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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